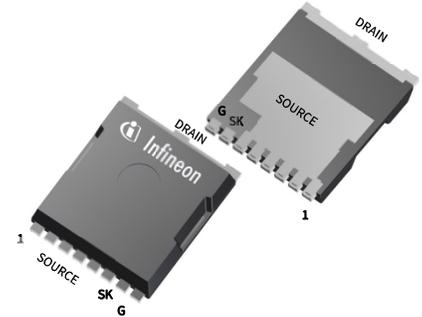


# IGT60R070D1

## 600V CoolGaN™ enhancement-mode Power Transistor

### Features

- Enhancement mode transistor – Normally OFF switch
- Ultra fast switching
- No reverse-recovery charge
- Capable of reverse conduction
- Low gate charge, low output charge
- Superior commutation ruggedness
- Qualified for industrial applications according to JEDEC Standards (JESD47 and JESD22)



### Benefits

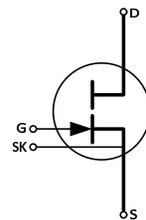
- Improves system efficiency
- Improves power density
- Enables higher operating frequency
- System cost reduction savings
- Reduces EMI

|               |               |
|---------------|---------------|
| Gate          | 8             |
| Drain         | drain contact |
| Kelvin Source | 7             |
| Source        | 1,2,3,4,5,6   |

### Applications

Industrial, telecom, datacenter SMPS based on the half-bridge topology (half-bridge topologies for hard and soft switching such as Totem pole PFC, high frequency LLC).

**For other applications:** review CoolGaN™ reliability white paper and contact Infineon regional support



**Table 1 Key Performance Parameters at T<sub>j</sub> = 25 °C**

| Parameter                | Value | Unit |
|--------------------------|-------|------|
| V <sub>DS,max</sub>      | 600   | V    |
| R <sub>DS(on),max</sub>  | 70    | mΩ   |
| Q <sub>G,typ</sub>       | 5.8   | nC   |
| I <sub>D,pulse</sub>     | 60    | A    |
| Q <sub>oss @ 400 V</sub> | 41    | nC   |
| Q <sub>rr</sub>          | 0     | nC   |



**Table 2 Ordering Information**

| Type / Ordering Code | Package     | Marking  | Related links  |
|----------------------|-------------|----------|----------------|
| IGT60R070D1          | PG-HSOF-8-3 | 60R070D1 | see Appendix A |

## Table of Contents

|   |    |
|---|----|
| Features .....                                    | 1  |
| Benefits .....                                    | 1  |
| Applications.....                                 | 1  |
| Table of Contents .....                           | 2  |
| 1       Maximum ratings .....                     | 3  |
| 2       Thermal characteristics .....             | 4  |
| 3       Electrical characteristics .....          | 5  |
| 4       Electrical characteristics diagrams ..... | 7  |
| 5       Test Circuits .....                       | 13 |
| 6       Package Outlines .....                    | 14 |
| 7       Appendix.....                             | 15 |
| 8       Revision History .....                    | 16 |

## 1 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

Continuous application of maximum ratings can deteriorate transistor lifetime. For further information, contact your local Infineon sales office.

**Table 3** Maximum ratings

| Parameter                                    | Symbol         | Values |      |      | Unit | Note/Test Condition  |
|--|----------------|--------|------|------|------|--|
|  |                | Min.   | Typ. | Max. |      |  |
| Drain Source Voltage <sup>1</sup>            | $V_{DS,max}$   | -      | -    | 600  | V    | $V_{GS} = 0\text{ V}$  |
| Continuous current, drain source             | $I_D$          | -      | -    | 31   | A    | $T_C = 25\text{ °C}; T_j = T_{j,max}$  |
|  |                | -      | -    | 20   |      | $T_C = 100\text{ °C}; T_j = T_{j,max}$   |
|  |                | -      | -    | 14   |      | $T_C = 125\text{ °C}; T_j = T_{j,max}$   |
| Pulsed current, drain source <sup>2 3</sup>  | $I_{D,pulse}$  | -      | -    | 60   | A    | $T_C = 25\text{ °C}; I_G = 26.1\text{ mA};$<br>See Figure 3; Figure 5;                                   |
| Pulsed current, drain source <sup>3 4</sup>  | $I_{D,pulse}$  | -      | -    | 35   | A    | $T_C = 125\text{ °C}; I_G = 26.1\text{ mA};$<br>See Figure 4; Figure 6;                                  |
| Gate current, continuous <sup>3 4 5</sup>    | $I_{G,avg}$    | -      | -    | 20   | mA   | $T_j = -55\text{ °C to }150\text{ °C};$  |
| Gate current, pulsed <sup>3 5</sup>          | $I_{G,pulse}$  | -      | -    | 2000 | mA   | $T_j = -55\text{ °C to }150\text{ °C};$<br>$t_{PULSE} = 50\text{ ns}, f=100\text{ kHz}$                  |
| Gate source voltage, continuous <sup>5</sup> | $V_{GS}$       | -10    | -    | -    | V    | $T_j = -55\text{ °C to }150\text{ °C};$  |
| Gate source voltage, pulsed <sup>5</sup>     | $V_{GS,pulse}$ | -25    | -    | -    | V    | $T_j = -55\text{ °C to }150\text{ °C};$<br>$t_{PULSE} = 50\text{ ns}, f = 100\text{ kHz};$<br>open drain |
| Power dissipation                            | $P_{tot}$      | -      | -    | 125  | W    | $T_C = 25\text{ °C}$   |
| Operating temperature                        | $T_j$          | -55    | -    | 150  | °C   |  |
| Storage temperature                          | $T_{stg}$      | -55    | -    | 150  | °C   | Max shelf life depends on storage conditions.  |
| Drain-source voltage slew-rate               | $dV/dt$        |        |      | 200  | V/ns |  |

<sup>1</sup> All devices are 100% tested at  $I_{DS} = 12.2\text{ mA}$  to assure  $V_{DS} \geq 800\text{ V}$

<sup>2</sup> Limits derived from product characterization, parameter not measured during production

<sup>3</sup> Ensure that average gate drive current,  $I_{G,avg}$  is  $\leq 20\text{ mA}$ . Please see figure 27 for  $I_{G,avg}$ ,  $I_{G,pulse}$  and  $I_G$  details

<sup>4</sup> Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

<sup>5</sup> We recommend using an advanced driving technique to optimize the device performance. Please see gate drive application note for details.

## 2 Thermal characteristics

Table 4 Thermal characteristics

| Parameter  | Symbol     | Values |      |      | Unit | Note/Test Condition  |
|--|------------|--------|------|------|------|--|
|  |            | Min.   | Typ. | Max. |      |  |
| Thermal resistance, junction-case                    | $R_{thJC}$ | -      | -    | 1    | °C/W |  |
| Thermal resistance, junction-ambient                 | $R_{thJA}$ | -      | -    | 62   | °C/W | Device on PCB, minimum footprint   |
| Thermal resistance, junction-ambient for SMD version | $R_{thJA}$ | -      | 35   | 45   | °C/W | Device on 40mm*40mm* 1.5mm epoxy PCB FR4 with 6cm <sup>2</sup> (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling. |
| Reflow soldering temperature                         | $T_{sold}$ | -      | -    | 245  | °C   | MSL3   |

### 3 Electrical characteristics

at  $T_j = 25\text{ °C}$ , unless specified otherwise

**Table 5 Static characteristics**

| Parameter   | Symbol       | Values     |                |            | Unit          | Note/Test Condition   |
|---|--------------|------------|----------------|------------|---------------|---|
|   |              | Min.       | Typ.           | Max.       |               |   |
| Gate threshold voltage  | $V_{GS(th)}$ | 0.9<br>0.7 | 1.2<br>1.0     | 1.6<br>1.4 | V             | $I_{DS} = 2.6\text{ mA}; V_{DS} = 10\text{ V}; T_j = 25\text{ °C}$<br>$I_{DS} = 2.6\text{ mA}; V_{DS} = 10\text{ V}; T_j = 125\text{ °C}$ |
| Drain-Source leakage current  | $I_{DSS}$    | -<br>-     | 1<br>20        | 100<br>-   | $\mu\text{A}$ | $V_{DS} = 600\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ °C}$<br>$V_{DS} = 600\text{ V}; V_{GS} = 0\text{ V}; T_j = 150\text{ °C}$     |
| Drain-Source leakage current at application conditions <sup>1</sup> | $I_{DSSapp}$ | -          | 60             | -          | $\mu\text{A}$ | $V_{DS} = 400\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$   |
| Gate-Source leakage current   | $I_{GSS}$    | -1<br>-1   | -<br>-         | -<br>-     | mA            | $V_{DS} = 0\text{ V}; V_{GS} = -10\text{ V}; T_j = 25\text{ °C}$<br>$V_{DS} = 0\text{ V}; V_{GS} = -10\text{ V}; T_j = 125\text{ °C}$     |
| Drain-Source on-state resistance                                    | $R_{DS(on)}$ | -<br>-     | 0.055<br>0.100 | 0.070<br>- | $\Omega$      | $I_G = 26.1\text{ mA}; I_D = 8\text{ A}; T_j = 25\text{ °C}$<br>$I_G = 26.1\text{ mA}; I_D = 8\text{ A}; T_j = 150\text{ °C}$             |
| Gate resistance   | $R_{G,int}$  | -          | 0.78           | -          | $\Omega$      | LCR impedance measurement;<br>$f = f_{res}$ ; open drain;   |

**Table 6 Dynamic characteristics**

| Parameter   | Symbol       | Values |       |      | Unit | Note/Test Condition   |
|---|--------------|--------|-------|------|------|---|
|   |              | Min.   | Typ.  | Max. |      |   |
| Input capacitance   | $C_{iss}$    | -      | 380   | -    | pF   | $V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$<br>$f = 1\text{ MHz}$               |
| Output capacitance  | $C_{oss}$    | -      | 72    | -    | pF   | $V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$<br>$f = 1\text{ MHz}$               |
| Reverse Transfer capacitance                              | $C_{rss}$    | -      | 0.3   | -    | pF   | $V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$<br>$f = 1\text{ MHz}$               |
| Effective output capacitance, energy related <sup>2</sup> | $C_{o(er)}$  | -      | 80    | -    | pF   | $V_{DS} = 0\text{ to }400\text{ V}$   |
| Effective output capacitance, time related <sup>3</sup>   | $C_{o(tr)}$  | -      | 102.5 | -    | pF   | $V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V};$<br>$I_D = \text{const}$ |
| Output charge   | $Q_{oss}$    | -      | 41    | -    | nC   | $V_{DS} = 0\text{ to }400\text{ V}$   |
| Turn- on delay time                                       | $t_{d(on)}$  | -      | 15    | -    | ns   | see Figure 23   |
| Turn- off delay time                                      | $t_{d(off)}$ | -      | 15    | -    | ns   | see Figure 23   |
| Rise time   | $t_r$        | -      | 9     | -    | ns   | see Figure 23   |
| Fall time   | $t_f$        | -      | 13    | -    | ns   | see Figure 23   |

<sup>1</sup> Parameter represents end of use leakage in applications

<sup>2</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400 V

<sup>3</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400 V

Table 7 Gate charge characteristics

| Parameter   | Symbol | Values |      |      | Unit | Note/Test Condition                                     |
|-------------|--------|--------|------|------|------|---|
|             |        | Min.   | Typ. | Max. |      |   |
| Gate charge | $Q_G$  | -      | 5.8  | -    | nC   | $I_{GS} = 0$ to 10 mA; $V_{DS} = 400$ V;<br>$I_D = 8$ A |

Table 8 Reverse conduction characteristics

| Parameter                     | Symbol        | Values |      |      | Unit | Note/Test Condition            |
|-------------------------------|---------------|--------|------|------|------|--------------------------------|
|                               |               | Min.   | Typ. | Max. |      |                                |
| Source-Drain reverse voltage  | $V_{SD}$      | -      | 2.2  | 2.5  | V    | $V_{GS} = 0$ V; $I_{SD} = 8$ A |
| Pulsed current, reverse       | $I_{S,pulse}$ | -      | -    | 60   | A    | $I_G = 26.1$ mA                |
| Reverse recovery charge       | $Q_{rr}^1$    | -      | 0    | -    | nC   | $I_S = 8$ A, $V_{DS} = 400$ V  |
| Reverse recovery time         | $t_{rr}$      | -      | 0    | -    | ns   |                                |
| Peak reverse recovery current | $I_{rrm}$     | -      | 0    | -    | A    |                                |

## 4 Electrical characteristics diagrams

at  $T_j = 25\text{ }^\circ\text{C}$ , unless specified otherwise

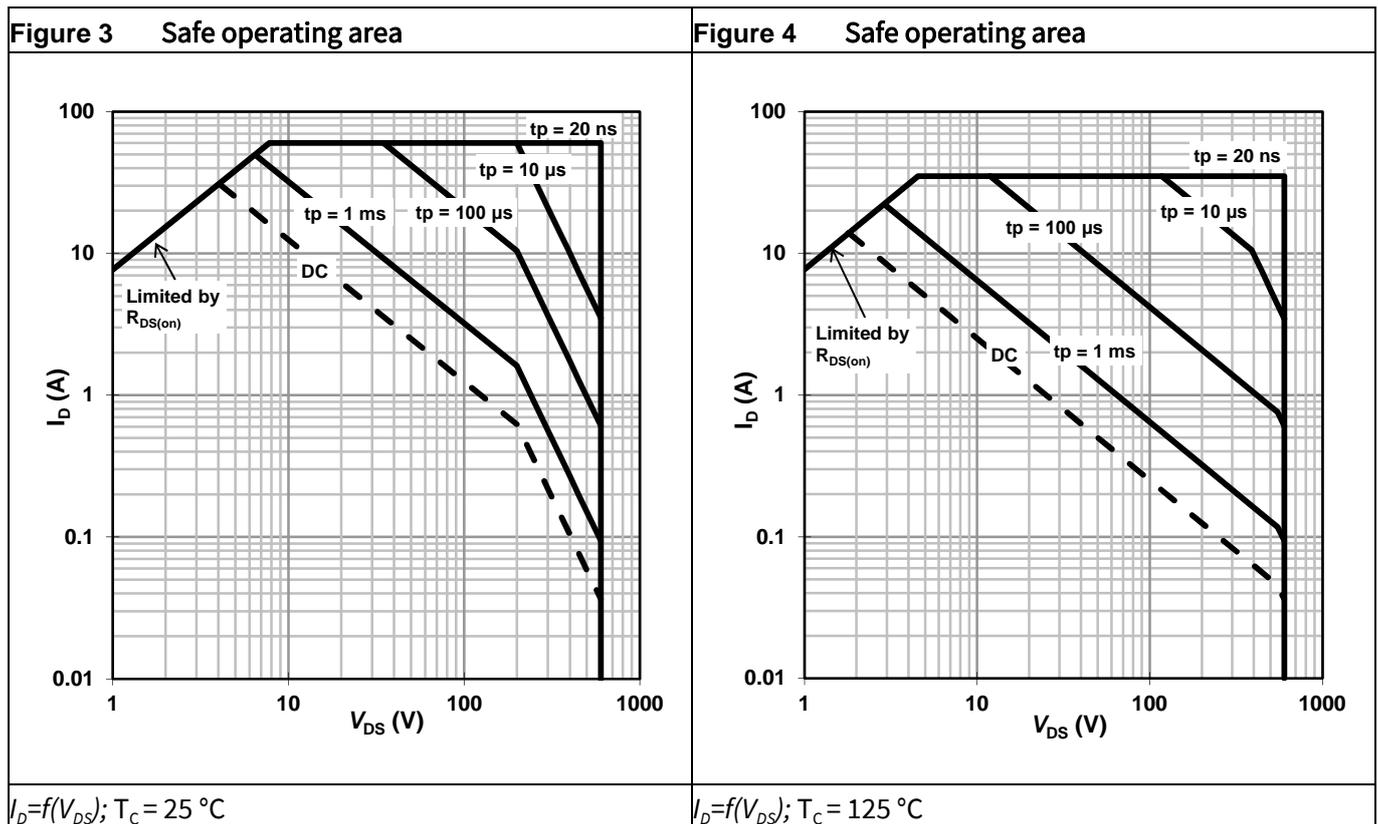
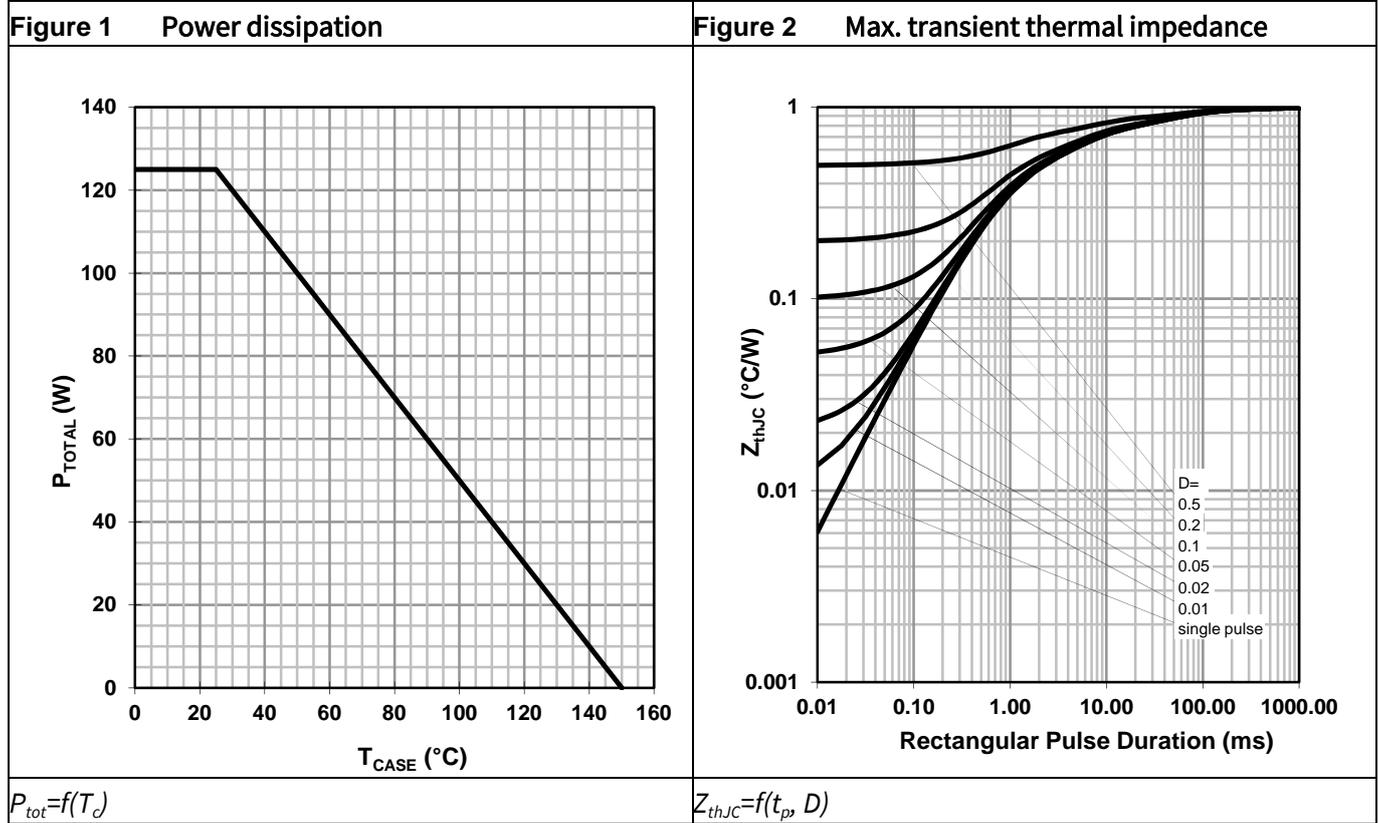
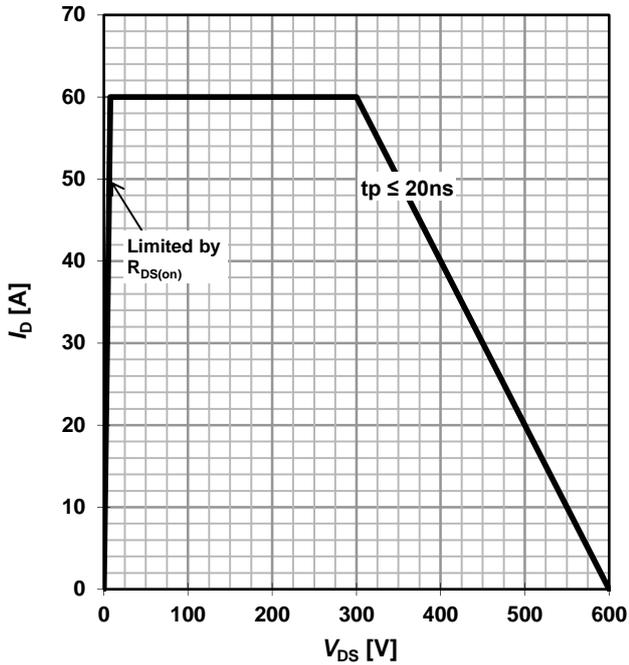
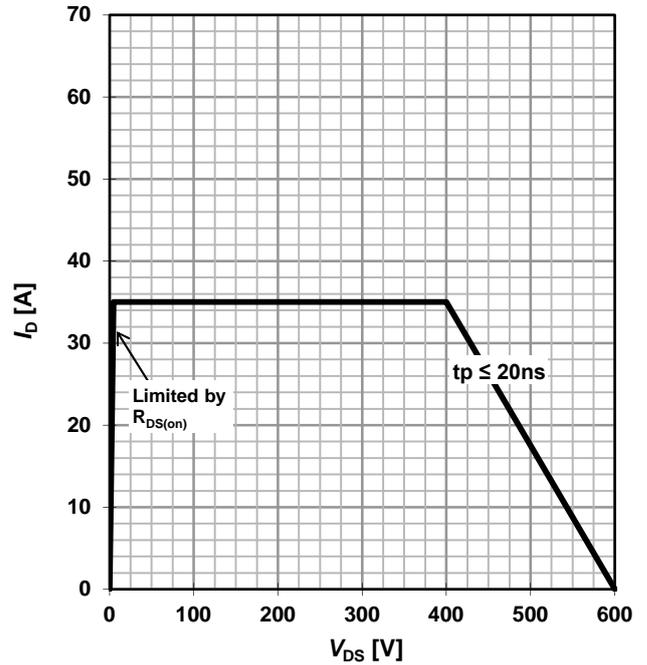


Figure 5 Repetitive safe operating area<sup>1</sup>



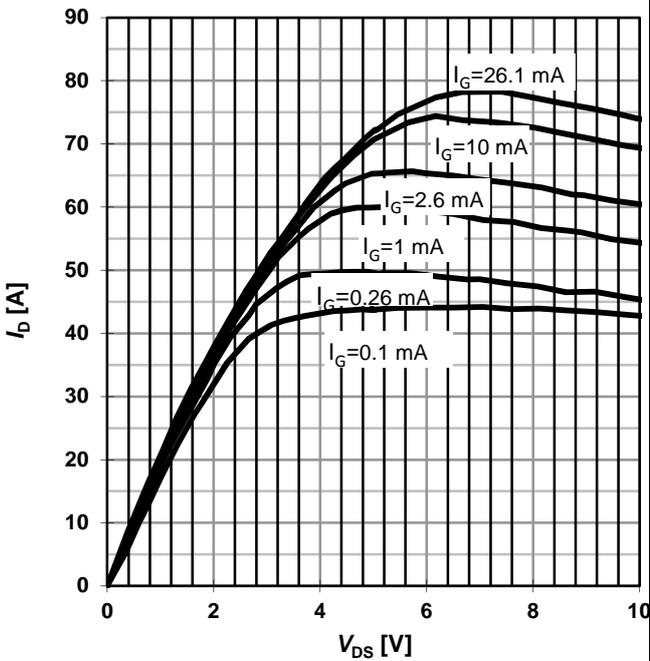
$T_c = 25\text{ °C}; T_j \leq 150\text{ °C}$

Figure 6 Repetitive safe operating area<sup>1</sup>



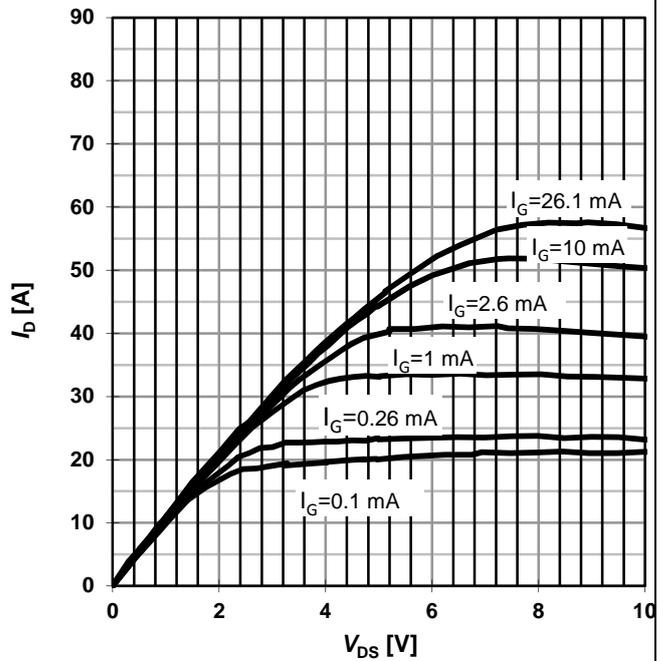
$T_c = 125\text{ °C}; T_j \leq 150\text{ °C}$

Figure 7 Typ. output characteristics



$I_D = f(V_{DS}, I_G); T_j = 25\text{ °C}$

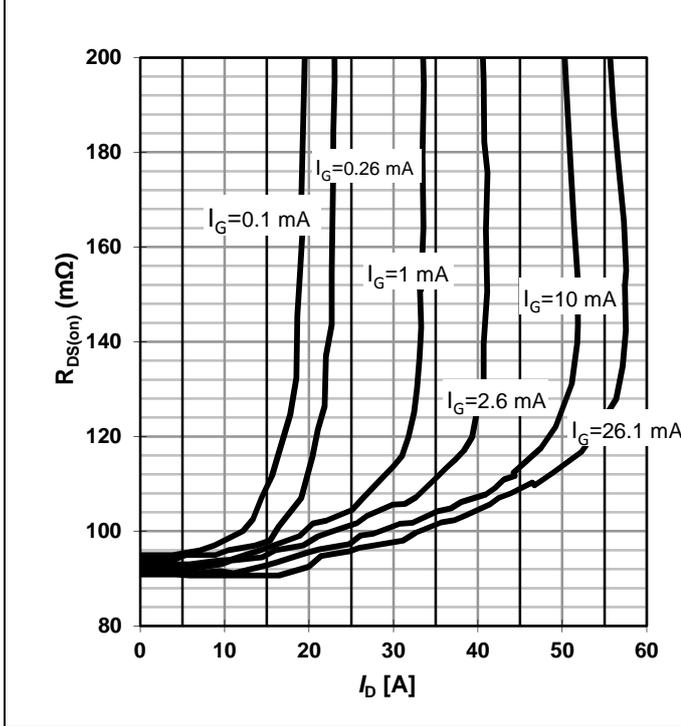
Figure 8 Typ. output characteristics



$I_D = f(V_{DS}, I_G); T_j = 125\text{ °C}$

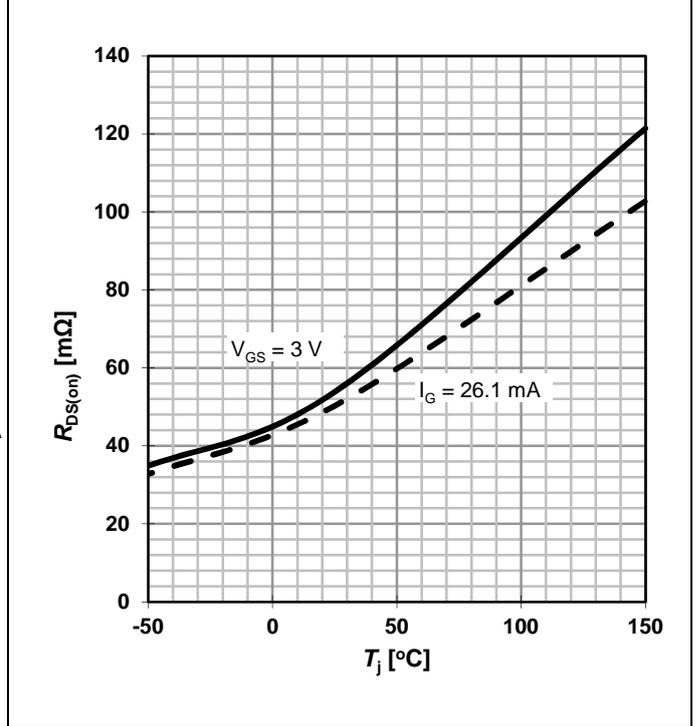
<sup>1</sup> Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

Figure 9 Typ. Drain-source on-state resistance



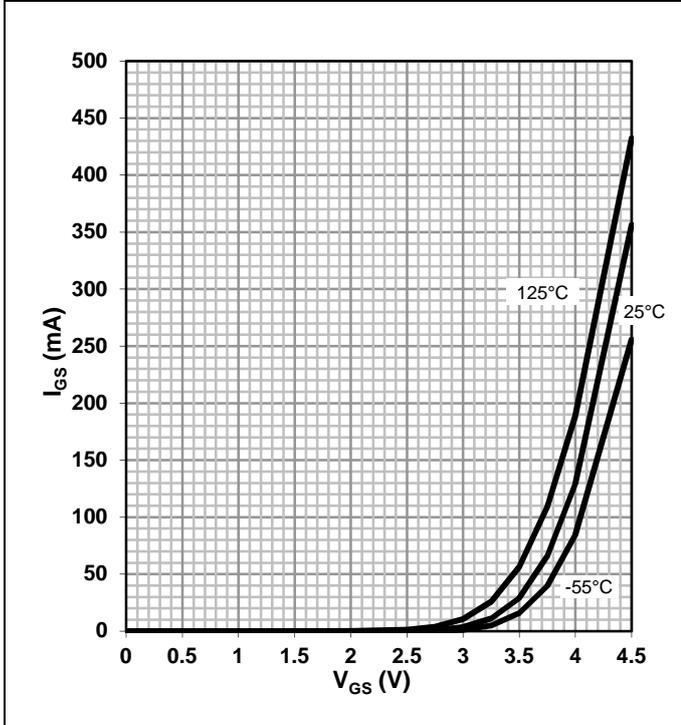
$R_{DS(on)} = f(I_D, I_G); T_j = 125^\circ\text{C}$

Figure 10 Drain-source on-state resistance



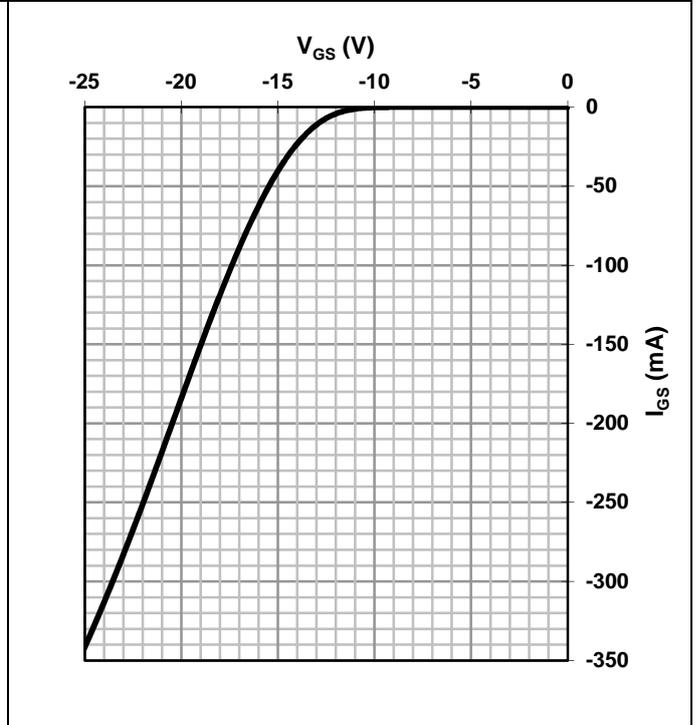
$R_{DS(on)} = f(T_j); I_D = 8\text{ A}$

Figure 11 Typ. gate characteristics forward



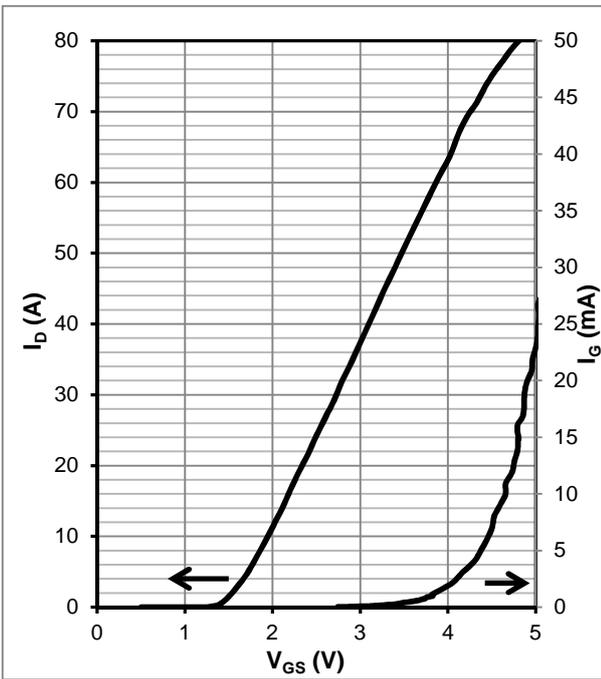
$I_{GS} = f(V_{GS}, T_j); \text{open drain}$

Figure 12 Typ. gate characteristics reverse



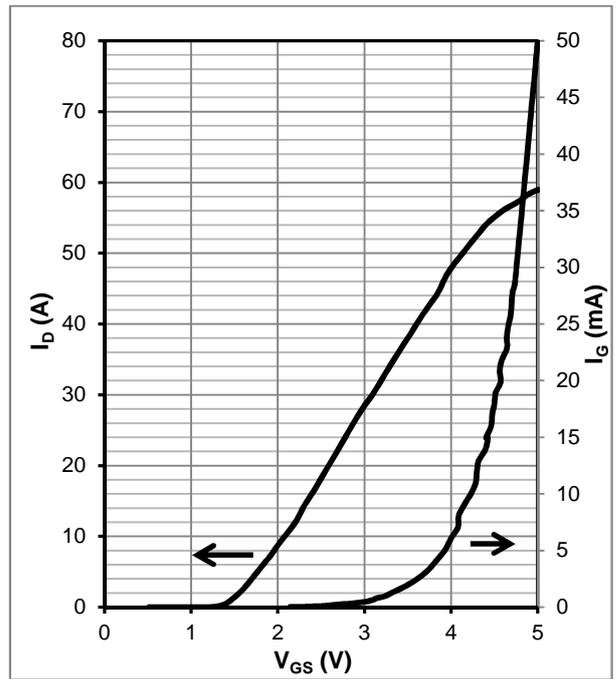
$I_{GS} = f(V_{GS}); T_j = 25^\circ\text{C}$

Figure 13 Typ. transfer characteristics



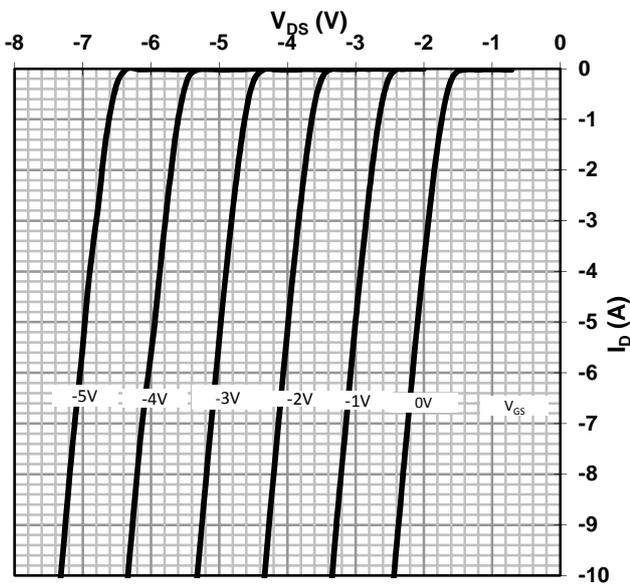
$I_D, I_G = f(V_{GS}); V_{DS} = 8 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$

Figure 14 Typ. transfer characteristics



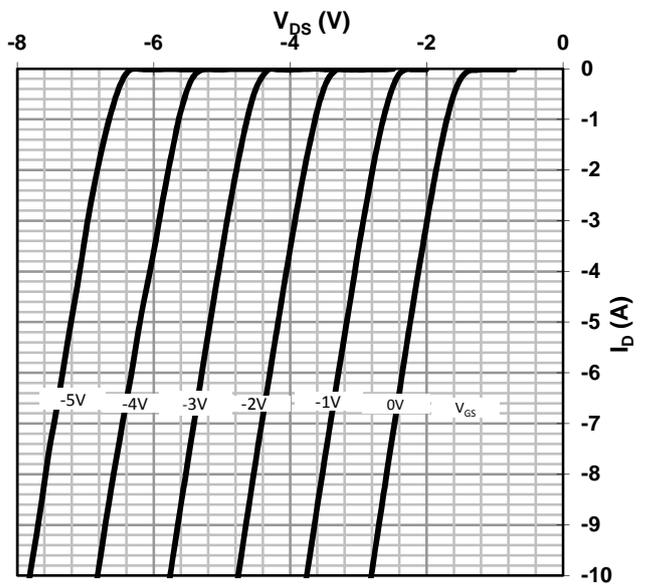
$I_D, I_G = f(V_{GS}); V_{DS} = 8 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$

Figure 15 Typ. channel reverse characteristics



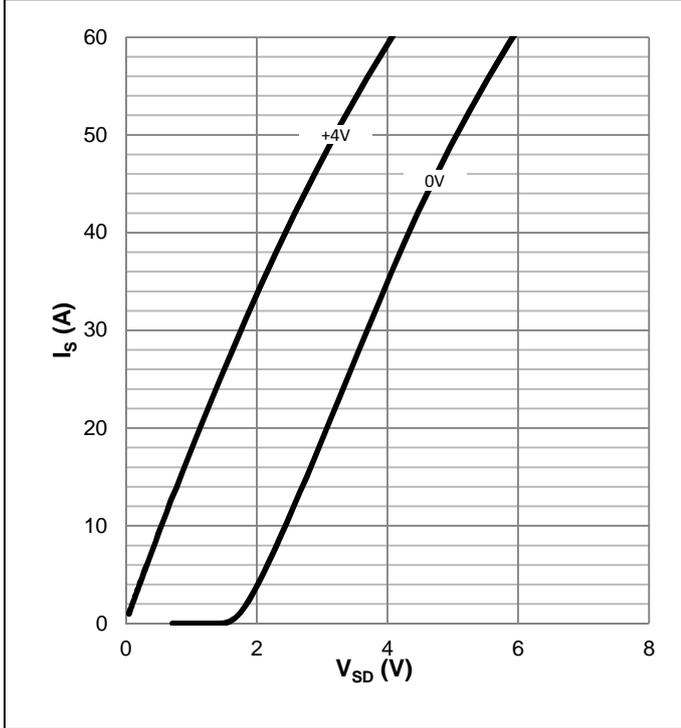
$V_{DS} = f(I_D, V_{GS}); T_j = 25 \text{ }^\circ\text{C}$

Figure 16 Typ. channel reverse characteristics



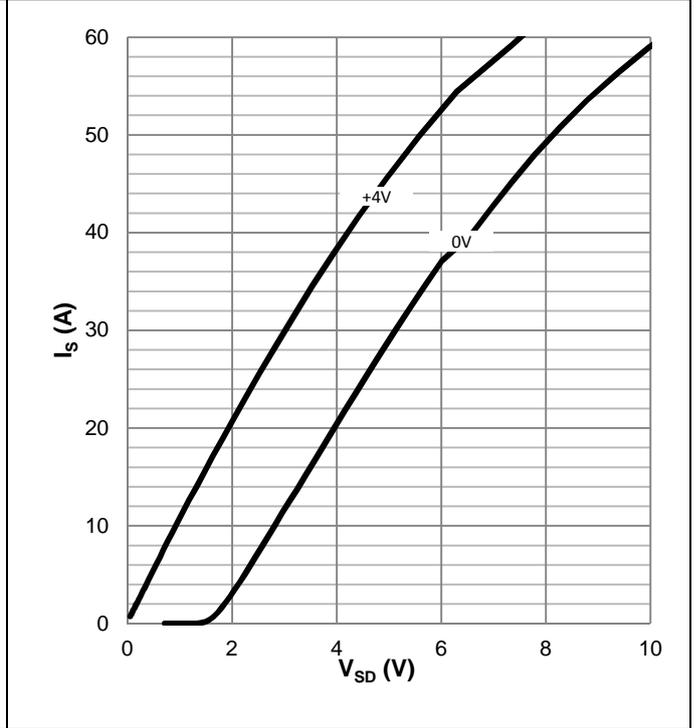
$V_{DS} = f(I_D, V_{GS}); T_j = 125 \text{ }^\circ\text{C}$

Figure 17 Typ. channel reverse characteristics



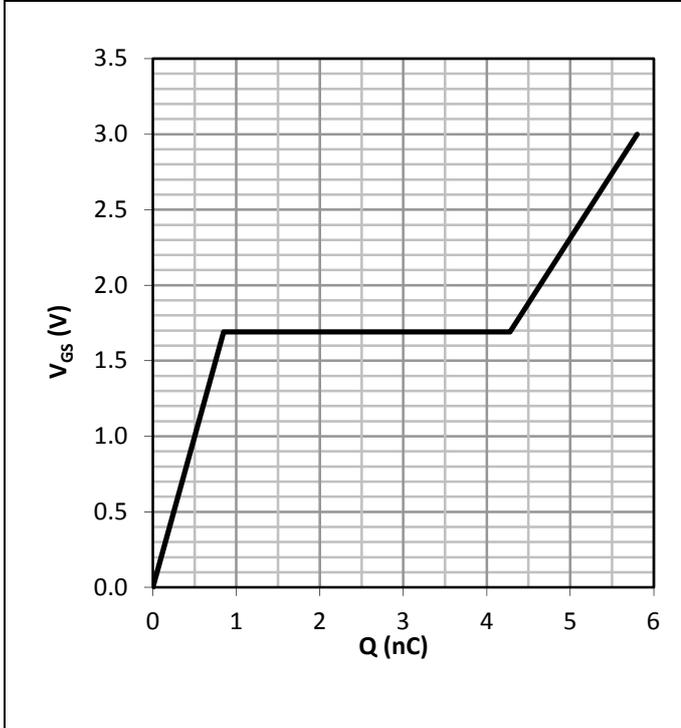
$I_D = f(V_{DS}, V_{GS}); T_j = 25\text{ °C}$

Figure 18 Typ. channel reverse characteristics



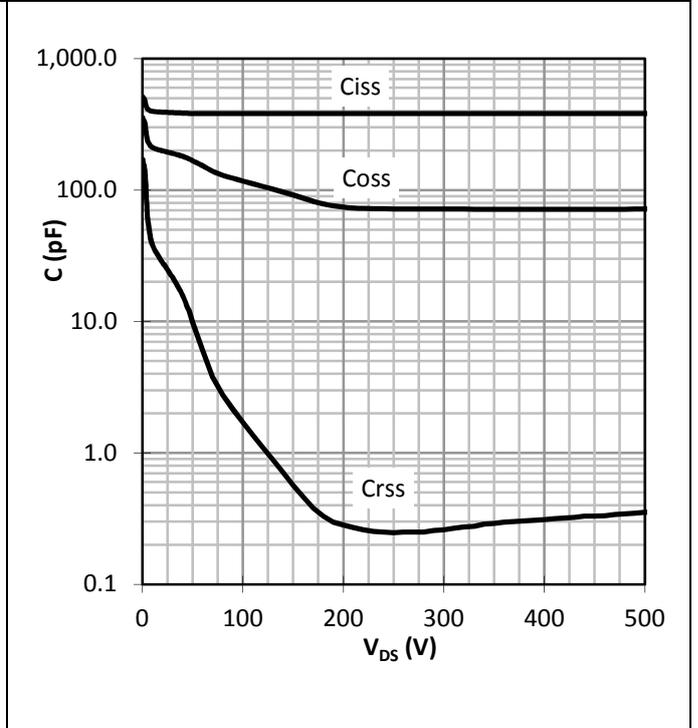
$I_D = f(V_{DS}, V_{GS}); T_j = 125\text{ °C}$

Figure 19 Typ. gate charge



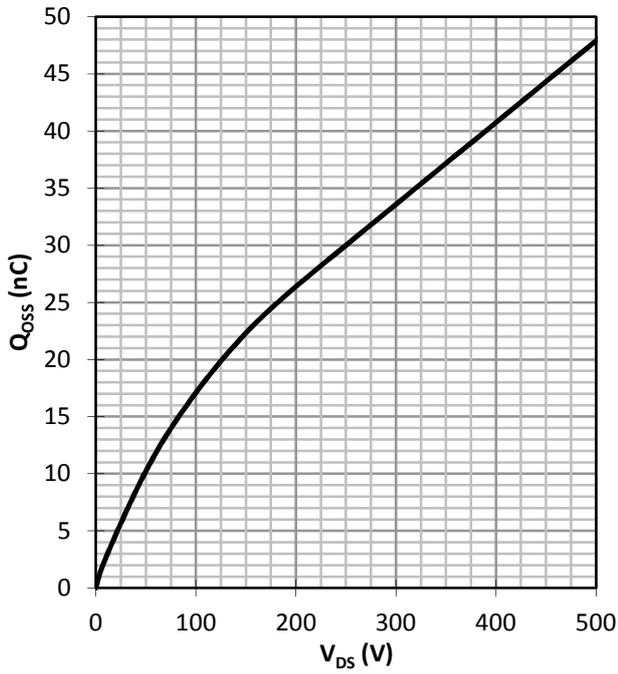
$V_{GS} = f(Q_G); V_{DCLINK} = 400\text{ V}; I_D = 8\text{ A}$

Figure 20 Typ. capacitances



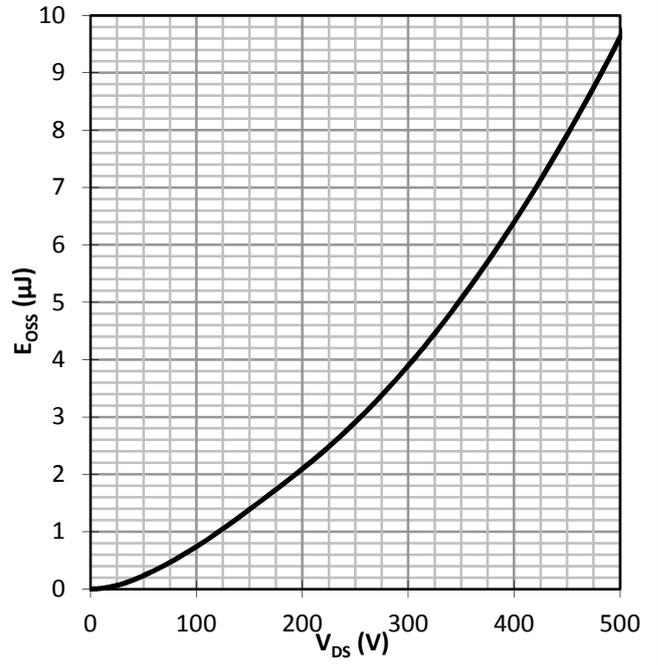
$C_{xSS} = f(V_{DS})$

Figure 21 Typ. output charge



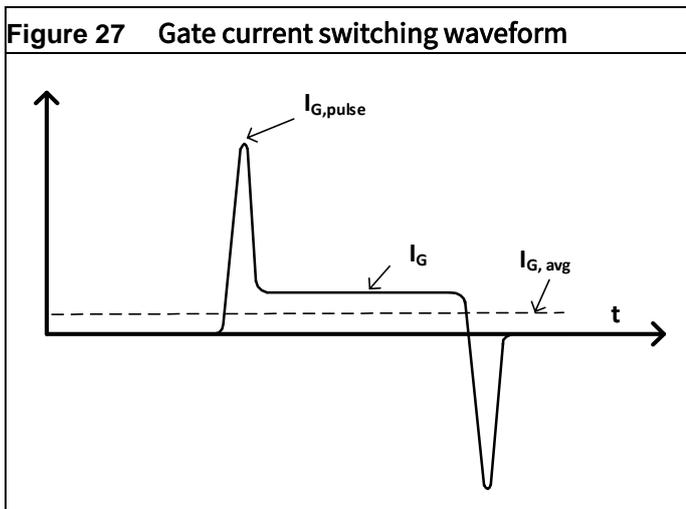
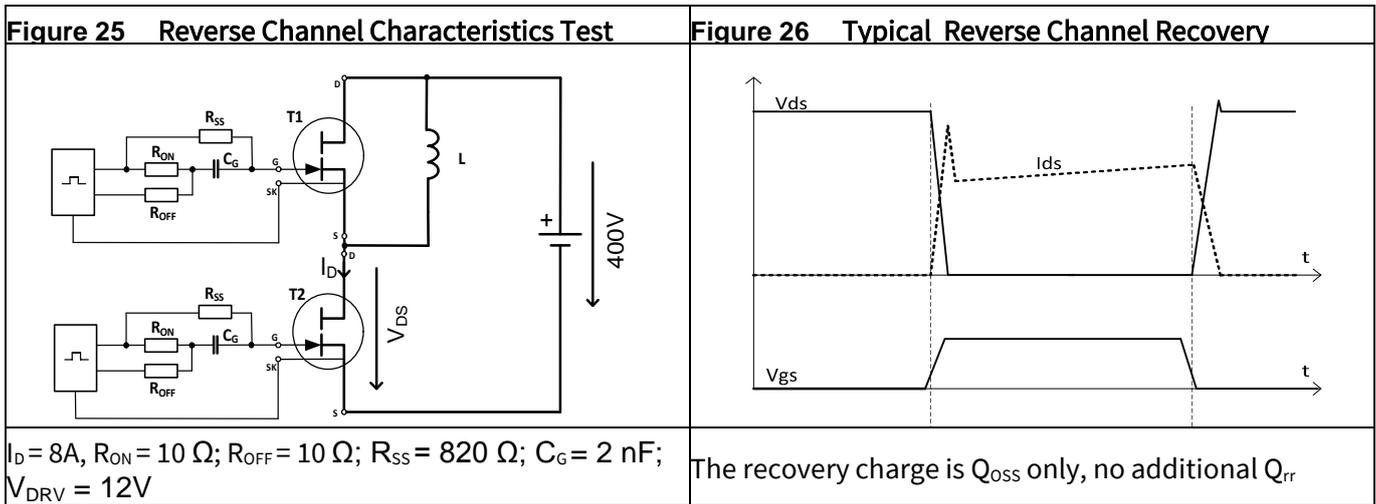
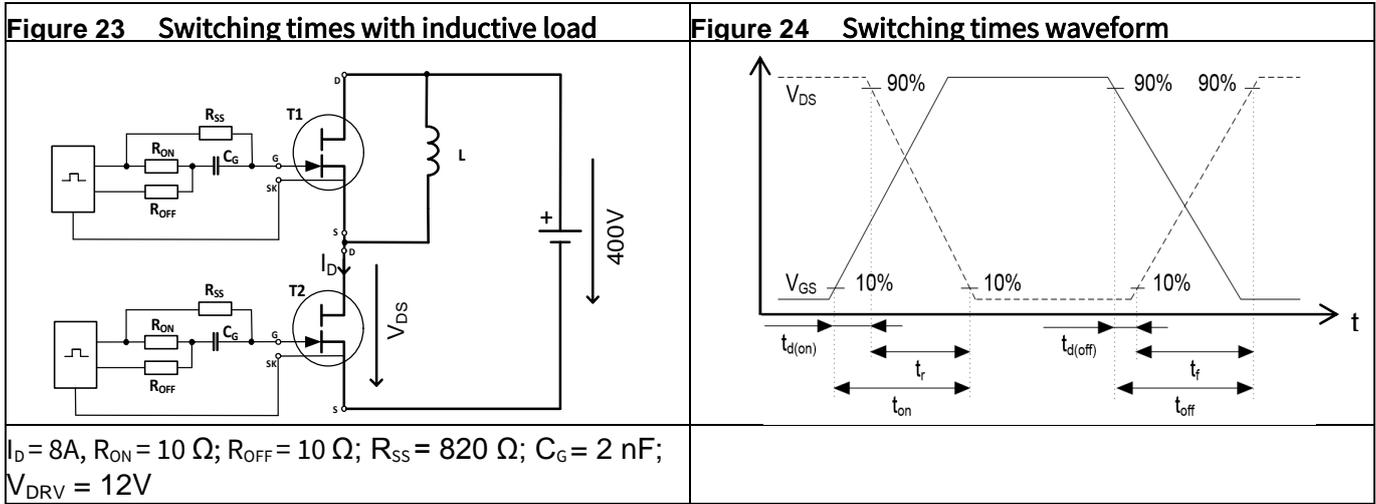
$Q_{oss} = f(V_{DS})$

Figure 22 Typ. Coss stored Energy



$E_{oss} = f(V_{DS})$

## 5 Test Circuits



## 6 Package Outlines

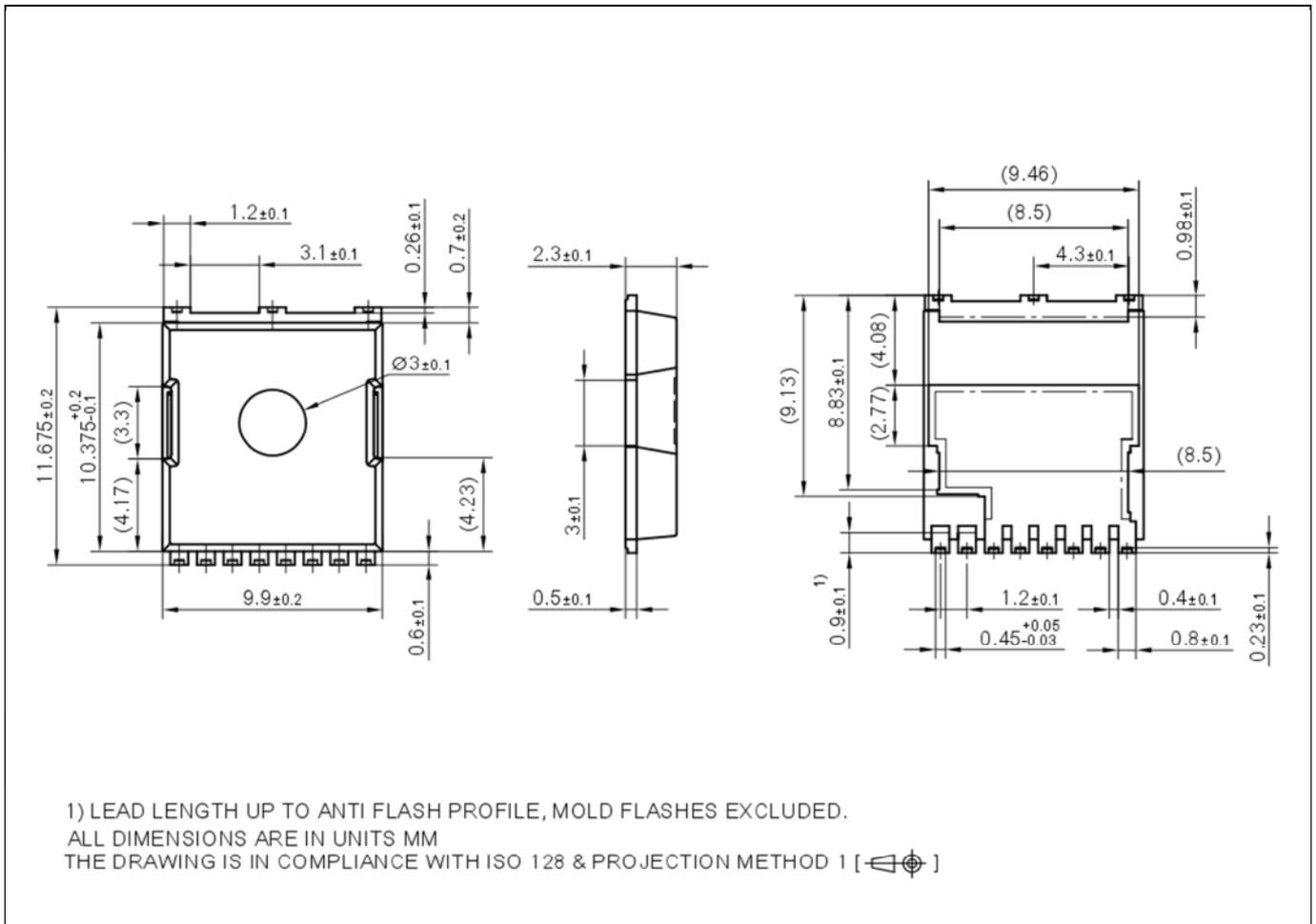


Figure 28 PG-HSOF-8-3 Package Outline, dimensions (mm)

## 7 Appendix A

### Table 9 Related links

- IFX CoolGaN™ webpage: [www.infineon.com/why-coolgan](http://www.infineon.com/why-coolgan)
- IFX CoolGaN™ reliability white paper: [www.infineon.com/gan-reliability](http://www.infineon.com/gan-reliability)
- IFX CoolGaN™ gate drive application note: [www.infineon.com/driving-coolgan](http://www.infineon.com/driving-coolgan)
- IFX CoolGaN™ applications information:
  - [www.infineon.com/gan-in-server-telecom](http://www.infineon.com/gan-in-server-telecom)
  - [www.infineon.com/gan-in-wirelesscharging](http://www.infineon.com/gan-in-wirelesscharging)
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  - [www.infineon.com/gan-in-adapter-charger](http://www.infineon.com/gan-in-adapter-charger)

## 8 Revision History

### Major changes since the last revision

| Revision | Date       | Description of change   |
|----------|------------|---|
| 2.0      | 2018-04-24 | Final version release   |
| 2.1      | 2018-10-12 | Updated application section; added Appendix A and Fig. 27; updated maximum rating table footnotes, switching times and figures. |
|          |            |   |

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